

forming [a step in which, after] a resist film [is formed] on the [aforementioned] first mask film, the resist film [is] being used as an etching mask to form an opening on the [aforementioned] first mask film, followed by the formation of trenches on the [aforementioned] insulating film exposed from the opening;

forming [a step in which], after the [aforementioned] resist film is removed, a second mask film [is formed] on the [aforementioned] semiconductor substrate or SOI substrate;

[a step in which, by] removing the [aforementioned] second mask film such that it is left on the side walls of the [aforementioned] trenches, a side wall made of the [aforementioned] second mask film is formed on the side walls of the [aforementioned] trenches;

and [a step in which] using the [aforementioned] first mask film and the [aforementioned] side wall [are used] as the etching mask in etching off the [aforementioned] insulating film exposed from the mask, so as to form connecting holes on the [aforementioned] insulating film.

2. (Amended) A manufacturing method of a semiconductor IC device [characterized by the fact that it consists of] comprising the following steps [of operation]:

forming [a step in which] an insulating film [is formed] on a semiconductor substrate or SOI substrate;

forming [a step in which] a first mask film [is formed] on the [aforementioned] insulating film;

forming [a step in which, after] a resist film [is formed] on the [aforementioned] first mask film, the resist film [is] being used as an etching mask to form an opening on the [aforementioned] first mask film, followed by the formation of trenches on the [aforementioned] insulating film exposed from the opening;

forming [a step in which], after the [aforementioned] resist film is removed, a second mask film [is formed] on the [aforementioned] semiconductor substrate or SOI substrate;

[a step in which, by] removing the [aforementioned] second mask film such that it is left on the side walls of the [aforementioned] trenches, a side wall made of the [aforementioned] second mask film is formed on the side walls of the [aforementioned] trenches;

using [a step in which] the [aforementioned] first mask film and the [aforementioned] side wall [are used] as the etching mask in etching off the [aforementioned] insulating film exposed from the mask, so as to form an opening on the [aforementioned] insulating film, followed by the formation of separating trenches on the [aforementioned] semiconductor substrate or SOI substrate exposed from the opening;

burying [and a step in which] an insulating film [is buried] in the [aforementioned] separating trenches to form a separating portion.

3. (Amended) A manufacturing method of a semiconductor IC device [characterized by the fact that it consists of] comprising the following steps [of operation]:

forming [a step in which] an insulating film [is formed] on a semiconductor substrate or SOI substrate;

forming [a step in which] a first mask film [is formed] on the [aforementioned] insulating film;

forming [a step in which, after] a resist film [is formed] on the [aforementioned] first mask film, the resist film [is] being used as an etching mask to form an opening on the [aforementioned] first mask film, followed by the formation of trenches on the [aforementioned] insulating film exposed from the opening;

forming [a step in which], after the [aforementioned] resist film is removed, a second mask film [is formed] on the [aforementioned] semiconductor substrate or SOI substrate;

[a step in which, by] removing the [aforementioned] second mask film such that it is left on the side walls of the [aforementioned] trenches, a side wall made of the [aforementioned] second mask film is formed on the side walls of the [aforementioned] trenches;

and [a step in which] using the [aforementioned] first mask film and the [aforementioned] side wall [are used] as the etching mask in etching off the [aforementioned] insulating film exposed from the mask, so as to form wiring-forming trenches on the [aforementioned] insulating film, followed by burying an electroconductive material in the [aforementioned] wiring-forming trenches to form a wiring layer made of the electroconductive material.

4. (Amended) The manufacturing method described in Claim 1, wherein [2, or 3, characterized by the fact that in this manufacturing method of a semiconductor IC device,] the [aforementioned] insulating film is selected from the group consisting of [refers to] a silica film, SOG film, PSG film, BPSG film, or a [laminated type] lamination consisting of these films, [with] the first mask film and second mask film for the [aforementioned [sic]]hook-shaped hard mask being selected from the group consisting of a polysilicon film, tungsten film, or other electroconductive film, or a silicon nitride film or other insulating film.

5. (Amended) The manufacturing method of a semiconductor IC device described in Claim 1, wherein [or 4, characterized by the fact that] the [aforementioned] connecting holes are in contact with

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Cont the lower electrodes in the capacitors of the memory cells, with the capacitors being set for storing information on the bit lines.

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Please add Claims 6-11 as follows:

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- 6. The manufacturing method of a semiconductor IC device described in Claim 4, wherein the connecting holes are in contact with the lower electrodes in the capacitors of the memory cells, with the capacitors being set for storing information on the bit lines.

7. The manufacturing method described in Claim 2, wherein the insulating film is selected from the group consisting of a silica film, SOG film, PSG film, BPSG film, or a lamination consisting of these films, the first mask film and second mask film for hook-shaped hard mask being selected from the group consisting of a polysilicon film, tungsten film, or other electroconductive film, or a silicon nitride film or other insulating film.

8. The manufacturing method of a semiconductor IC device described in Claim 7, wherein the connecting holes are in contact with the lower electrodes in the capacitors of the memory cells, with the capacitors being set for storing information on the bit lines.

9. The manufacturing method described in Claim 3, wherein the insulating film is selected from the group consisting of a silica film, SOG film, PSG film, BPSG film, or a lamination consisting of these films, the first mask film and second mask film for hook-shaped hard mask being selected from the group consisting of a polysilicon film, tungsten film, or other electroconductive film, or a silicon nitride film or other insulating film.